

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

Listing of Claims:

Claim 1 (currently amended): A nickel alloy sputtering target for forming a film for preventing Sn diffusion, comprising: 1 to 30at% of Cu; 2 to 25at% of at least one element selected from among V, Cr, Al, Si, ~~Ti~~ and Mo; remnant Ni and unavoidable impurities ~~so as to inhibit the Sn diffusion between a solder bump and a substrate layer or a pad.~~

Claim 2 (currently amended): The nickel alloy sputtering target according to claim 1, wherein the nickel alloy is formed by adding said at least one element selected from among V, Cr, Al, Si, ~~Ti~~ and Mo to a Ni-Cu solid solution.

Claim 3 (canceled).

Claim 4 (original): A nickel alloy thin film formed between a solder bump and a substrate layer or a pad, and comprising 1 to 30at% of Cu; 2 to 25at% of at least one element selected from among V, Cr, Al, Si, Ti and Mo; remnant Ni and unavoidable impurities.

Claim 5 (currently amended): The nickel alloy thin film formed between a solder bump and a substrate layer or a pad according to claim 4, wherein the nickel alloy is formed by adding said at least one element selected from among V, Cr, Al, Si, Ti and Mo to a Ni-Cu solid solution.

Claims 6-8 (canceled).

Claim 9 (new): A nickel alloy thin film according to claim 5, wherein the solder bump is a Pb-free Sn solder or a Sn solder.

Claim 10 (new): A nickel alloy thin film according to claim 9, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 11 (new): A nickel alloy thin film according to claim 10, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 12 (new): A nickel alloy thin film according to claim 4, wherein the solder bump is a Pb-free Sn solder or a Sn solder.

Claim 13 (new): A nickel alloy thin film according to claim 12, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 14 (new): A nickel alloy thin film according to claim 13, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 15 (new): A nickel alloy thin film according to claim 4, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 16 (new): A nickel alloy thin film according to claim 15, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 17 (new): The nickel alloy sputtering target according to claim 2, further comprising Ti, wherein a total amount of Ti together with said at least one element selected from among V, Cr, Al, Si and Mo is 2 to 25at%.

Claim 18 (new): The nickel alloy sputtering target according to claim 1, further comprising Ti, wherein a total amount of Ti together with said at least one element selected from among V, Cr, Al, Si and Mo is 2 to 25at%.